IN THE CLAIMS:

1. (Original) A light-emitting device comprising:

a wiring formed on a first film;

a second film formed of the same layer as the wiring on the first film;

a third film formed over the first film; and

an electrode of a light-emitting element formed on the third film,

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film, and

wherein an opening of a fourth film covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the second film.

2. (Original) The light-emitting device according to claim 1, wherein a reflective film is included in the electrode of the light-emitting element.

3. (Original) The light-emitting device according to claim 1 or claim 2, wherein the wiring is integrated with the second film.

4. (Original) The light-emitting device according to claim 1, wherein the second film has a film thickness equal to or thicker than that of the wiring.

5. (Currently Amended) A light-emitting device comprising:

a transistor including a semiconductor film, a gate insulating film, and a gate electrode;

a first film formed on the transistor;

a wiring formed on the first film;

a second film formed of the same layer as the wiring on the first film;

a third film formed over the first film; and

an electrode of a light-emitting element formed on the third film,

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film, and

wherein an opening of a fourth film covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the second film.

6. (Original) The light-emitting device according to claim 5, wherein a reflective film is included in the electrode of the light-emitting element.

7. (Original) The light-emitting device according to claim 5 or claim 6, wherein the wiring is integrated with the second film.

8. (Original) The light-emitting device according to claim 5, wherein the second film has a film thickness equal to or thicker than that of the wiring.

9. (Currently Amended) A light-emitting device comprising:

a semiconductor film;

a gate insulating film formed on the semiconductor film;

a gate electrode formed on the gate insulating film;

a first film formed on the gate electrode;

a wiring formed on the first film;

a second film formed of the same layer as the wiring on the first film;

a third film formed over the first film; and

an electrode of a light-emitting element formed on the third film,

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film, and

wherein an opening of a fourth film covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the second film.

10. (Original) The light-emitting device according to claim 9, wherein a reflective film is provided in the electrode of the light-emitting element.

11. (Original) The light-emitting device according to claim 9 or claim 10, wherein the wiring is integrated with the second film.

12. (Original) The light-emitting device according to claim 9, wherein the second film has a film thickness equal to or thicker than that of the wiring.

13. (Original) A light-emitting device comprising:

a wiring formed on a first interlayer insulating film;

a conductive film formed of the same layer as the wiring on the first interlayer insulating film;

a second interlayer insulating film formed over the first interlayer insulating film; and

an electrode of a light-emitting element formed on the second interlayer insulating film;

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the conductive film, and

wherein an opening of a partition layer covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the conductive film.

14-17. (Cancelled)